MJ15022 (NPN), MJ15024 (NPN)

Silicon Power Transistors

The MJ15022 and MJ15024 are power transistors designed for high power audio, disk head positioners and other linear applications.

Features

- High Safe Operating Area
- High DC Current Gain
- These Devices are Pb-Free and are RoHS Compliant*
- Complementary to MJ15023 (PNP), MJ15025 (PNP)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJ15022 MJ15024	V _{CEO}	200 250	Vdc
Collector-Base Voltage MJ15022 MJ15024	V _{CBO}	350 400	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector-Emitter Voltage	V_{CEX}	400	Vdc
Collector Current - Continuous	I _C	16	Adc
Collector Current - Peak (Note 1)	I _{CM}	30	Adc
Base Current - Continuous	Ι _Β	5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle \leq 10%.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	°C/W

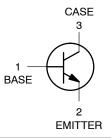


ON Semiconductor®

http://onsemi.com

16 AMPERES SILICON POWER TRANSISTORS 200 – 250 VOLTS, 250 WATTS

SCHEMATIC





TO-204AA (TO-3) CASE 1-07 STYLE 1

MARKING DIAGRAM



MJ1502x = Device Code

x = 2 or 4

G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
MJ15022G	TO-204 (Pb-Free)	100 Units / Tray
MJ15024G	TO-204 (Pb-Free)	100 Units / Tray

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MJ15022 (NPN), MJ15024 (NPN)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					U
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 100 \text{ mAdc}, I_B = 0)$	MJ15022 MJ15024	V _{CEO(sus)}	200 250	- -	_
Collector Cutoff Current $(V_{CE} = 200 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 250 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc})$	MJ15022 MJ15024	I _{CEX}	- -	250 250	μAdc
Collector Cutoff Current $(V_{CE} = 150 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 200 \text{ vdc}, I_B = 0)$	MJ15022 MJ15024	I _{CEO}	- -	500 500	μAdc
Emitter Cutoff Current (V _{CE} = 5 Vdc, I _B = 0)		I _{EBO}	-	500	μAdc
SECOND BREAKDOWN					u
Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 50 Vdc, t = 0.5 s (non-repetitive)) (V _{CE} = 80 Vdc, t = 0.5 s (non-repetitive))		I _{S/b}	5 2	_ _	Adc
ON CHARACTERISTICS			·	1	
DC Current Gain $(I_C = 8 \text{ Adc}, V_{CE} = 4 \text{ Vdc})$ $(I_C = 16 \text{ Adc}, V_{CE} = 4 \text{ Vdc})$		h _{FE}	15 5	60 -	-
Collector–Emitter Saturation Voltage ($I_C = 8$ Adc, $I_B = 0.8$ Adc) ($I_C = 16$ Adc, $I_B = 3.2$ Adc)		V _{CE(sat)}		1.4 4.0	Vdc
Base-Emitter On Voltage (I _C = 8 Adc, V _{CE} = 4 Vdc)		V _{BE(on)}	-	2.2	Vdc
DYNAMIC CHARACTERISTICS				•	•
Current-Gain - Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz)		f _T	4	_	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f_{test} = 1 \text{ MHz})$		C _{ob}	_	500	pF

^{2.} Pulse Test: Pulse Width = 300 μs , Duty Cycle \leq 2%.

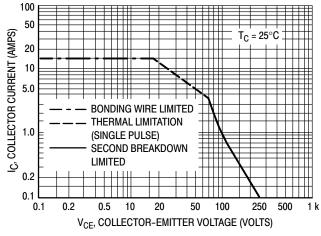


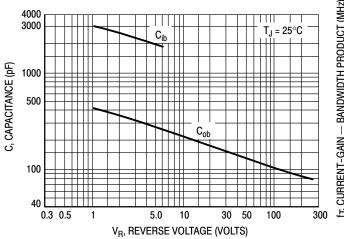
Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 200^{\circ}\text{C}$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values Ion than the limitations imposed by second breakdown.

MJ15022 (NPN), MJ15024 (NPN)

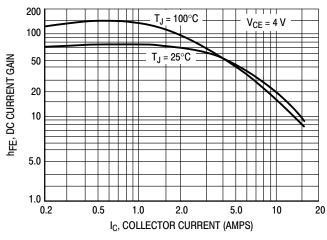
TYPICAL CHARACTERISTICS



T_J = 25°C V_{CE} = 10 V V_{Test} = 1 MHz T_{Test} = 1 MHz T_{Tes}

Figure 2. Capacitances

Figure 3. Current-Gain — Bandwidth Product



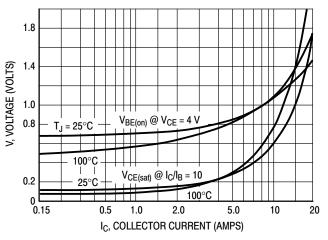


Figure 4. DC Current Gain

Figure 5. "On" Voltage

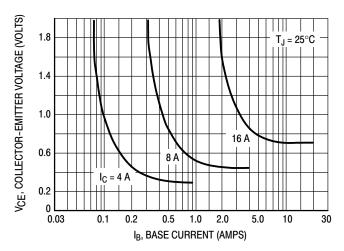
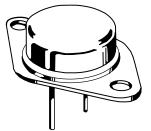


Figure 6. Collector Saturation Region

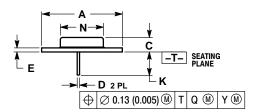


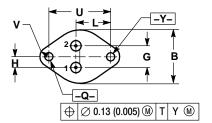


TO-204 (TO-3) **CASE 1-07 ISSUE Z**

DATE 05/18/1988







- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.550	1.550 REF		REF
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430	0.430 BSC		BSC
Н	0.215 BSC		5.46	BSC
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89	BSC
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15	BSC
٧	0.131	0.188	3.33	4.77

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR	STYLE 2: PIN 1. BASE 2. COLLECTOR CASE: EMITTER	STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN	STYLE 4: PIN 1. GROUND 2. INPUT CASE: OUTPUT	STYLE 5: PIN 1. CATHODE 2. EXTERNAL TRIP/DELAY CASE: ANODE
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	
PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE #1	PIN 1. ANODE #1	
2. EMITTER	2. OPEN	2. CATHODE #2	2. ANODE #2	
CASE: COLLECTOR	CASE: CATHODE	CASE: ANODE	CASE: CATHODE	

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